

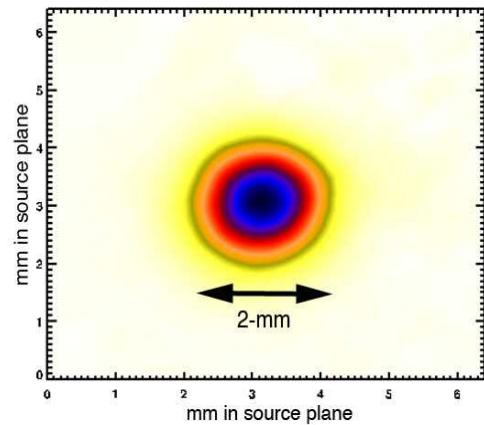
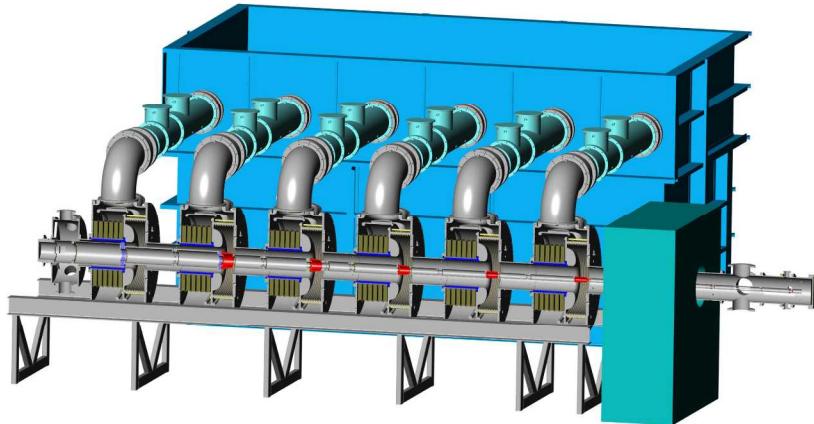
# Recent Advances in Radiographic X-ray Source Development at Sandia\*

SAND2008-4473P

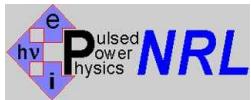
B.V. Oliver

*Sandia National Laboratories, Albuquerque, NM 87185, USA*

presented at the  
17<sup>th</sup> Intl. Conf. on High Power Particle  
Xian, China  
July 7-11, 2008



\*In collaboration with the Atomic Weapons Establishment U.K., Naval Research Laboratories, Los Alamos, NSTec, and Voss Scientific:



Sandia is a multiprogram laboratory operated by Sandia Corporation, a Lockheed Martin Company, for the United States Department of Energy's National Nuclear Security Administration under contract DE-AC04-94AL85000.

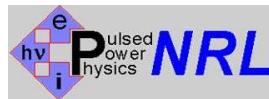


# Acknowledgements

We have a large number of collaborators on pulsed-power driven radiographic diode research:



K. Hahn  
M. Johnston  
J. Leckbee  
J. Maenchen  
I. Molina  
S. Cordova  
D. Rovang  
S. Portillo  
E. Ormand



G. Cooperstein  
R. Commisso  
D. Hinshelwood  
D. Mosher  
P. Ottinger  
S. Strausberg  
S. Swanekamp (L-3)  
J. Schumer  
B. Weber  
F. Young (L-3)



J. O'Malley  
D. Short  
A. Birrell  
G. Cooper  
J. McClean  
M. Sinclair  
J. Threadgold  
P. Martin  
A. Critchley  
T. Goldsack

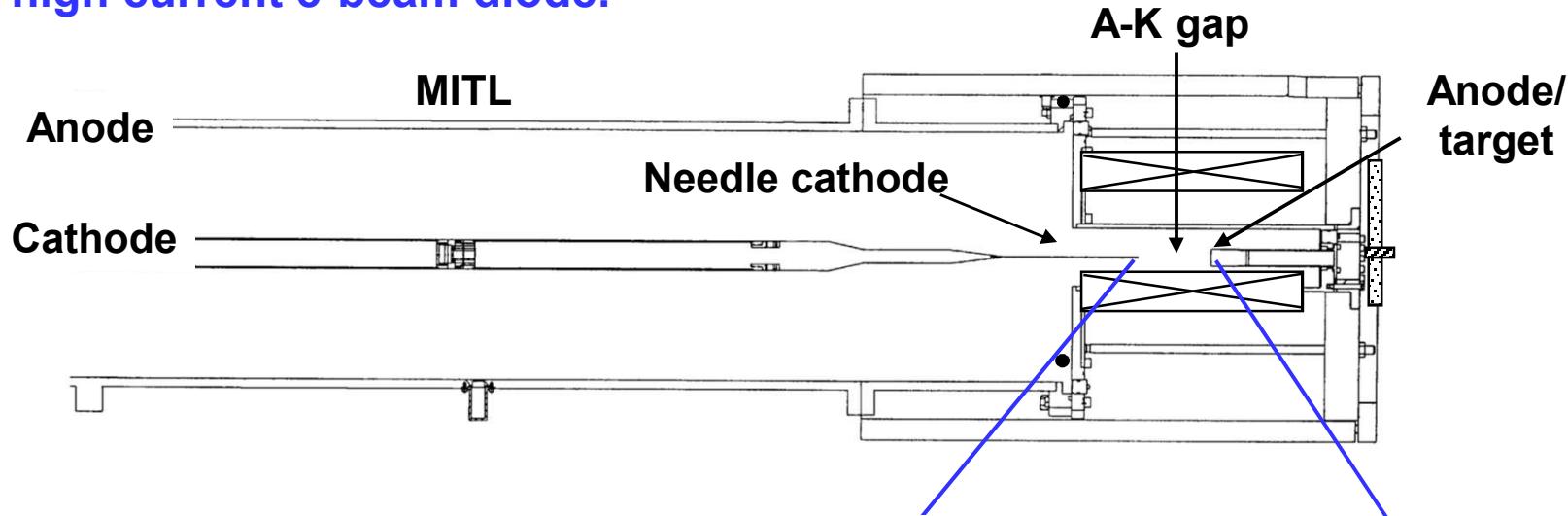
## Others

E. Schamiloglu (UNM)  
J. Smith (LANL)  
D. Droemer (NSTec)  
D. Rose (Voss)  
D. Welch (Voss)  
N. Bruner (Voss)

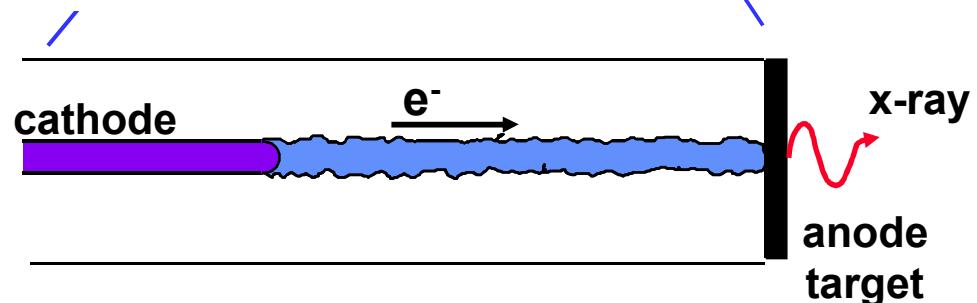
I. Smith (L-3)  
D. Johnson (L-3)  
V. Bailey (L-3)  
P. Corcoran (L-3)

# Inductive Voltage Adder (IVA) based e-beam driven radiography

The electron beam is created in the accelerating gap of a high current e-beam diode.



Bremmstrahlung x-rays are created when the e-beam is stopped in a high atomic number converter.



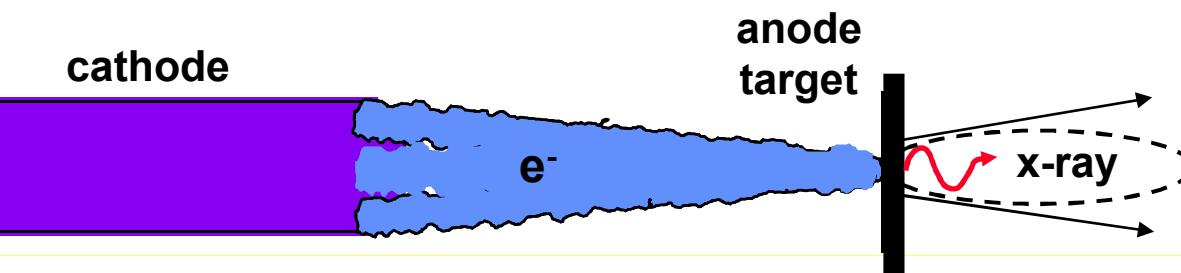
Energy = 2-10 MeV, Current = 20-150 kA, Pulse length = 50-100ns

# Some General Beam/Radiation Principles

Radiation dose/flux:

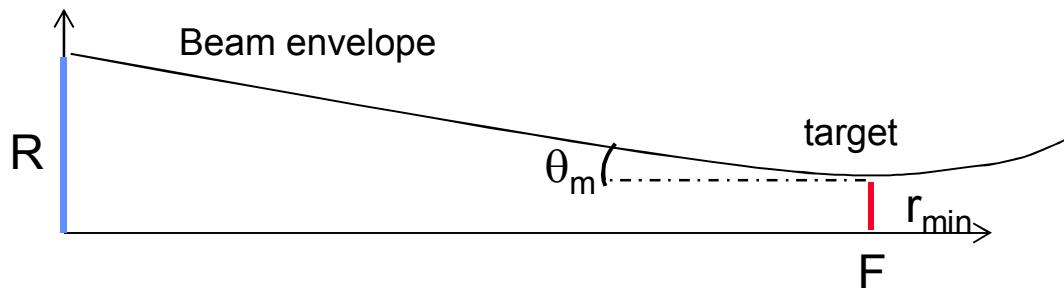
$$\propto \int dt \ I_b \ V^\alpha, \quad 1 < \alpha < 3$$

related to the beam current  $I$  and voltage  $V$ .



x-rays are forward directed within an angle  $\propto 1/\gamma$ .  $\alpha$  is dependent on beam angles of incidence and temperature.

Radiation spot size: equivalent to the beam spot on target.



Spots are limited by beam emittance/micro-divergence

$$r_{\min} \cong \theta_\mu F, \quad \theta_m \cong R/F$$
$$\theta_\mu = \frac{1}{\sqrt{\pi}} \frac{\epsilon}{R}$$

# Optimization of radiographic performance

A figure of merit (FOM) for the diode radiographic utility is quantified by the photon intensity, defined as:

$$\text{FOM} = \text{Dose/spot}^2 \quad \text{rads@m/mm}^2$$

To increase the FOM one must either decrease spot, increase dose or both.

Smaller spots are achieved by:

- increasing beam macro-angle  $\theta_m$  at target
- decreasing beam emittance/micro-divergence  $\varepsilon, \theta_\mu$

**Conflicting requirements**

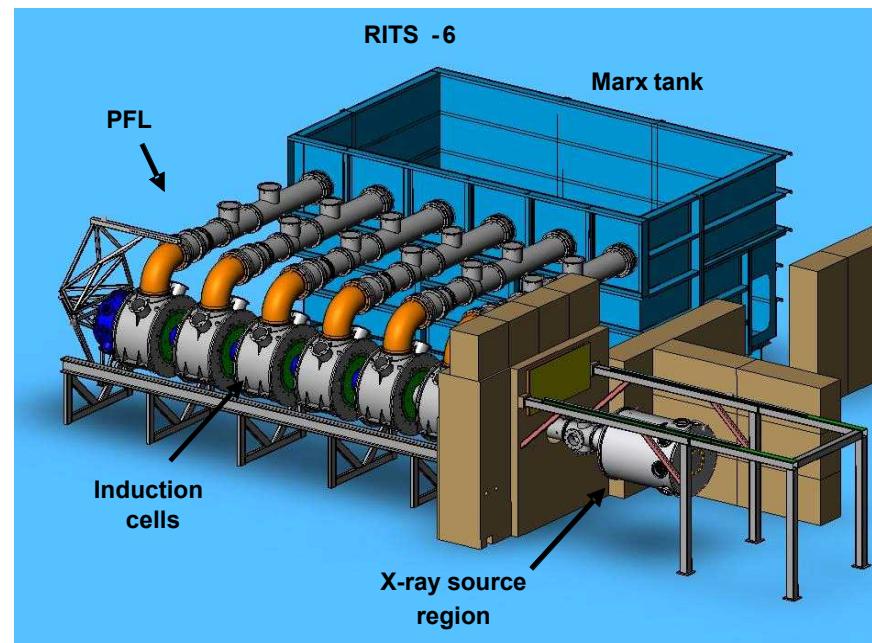
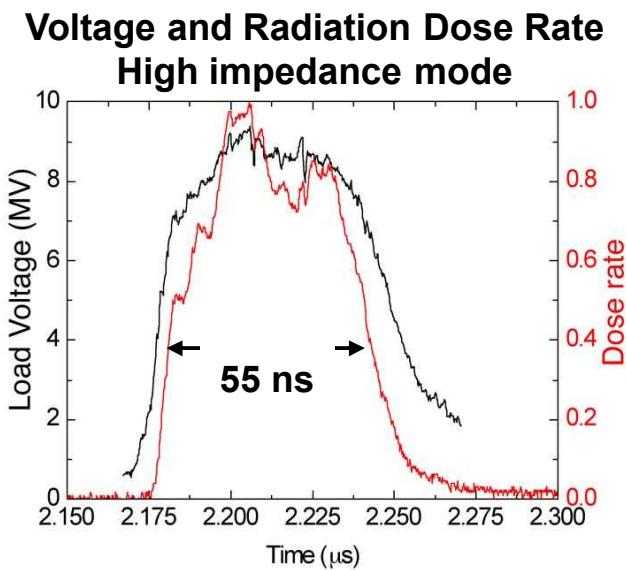
Larger dose is achieved by:

- decreasing beam macro-angle  $\theta_m$  at target
- increasing beam energy and or current (V, I)

# Experiments are fielded on the Radiographic Integrated Test Stand RITS-6

E-beam driven x-ray radiography test stand based on Induction Voltage Adder (IVA) technology

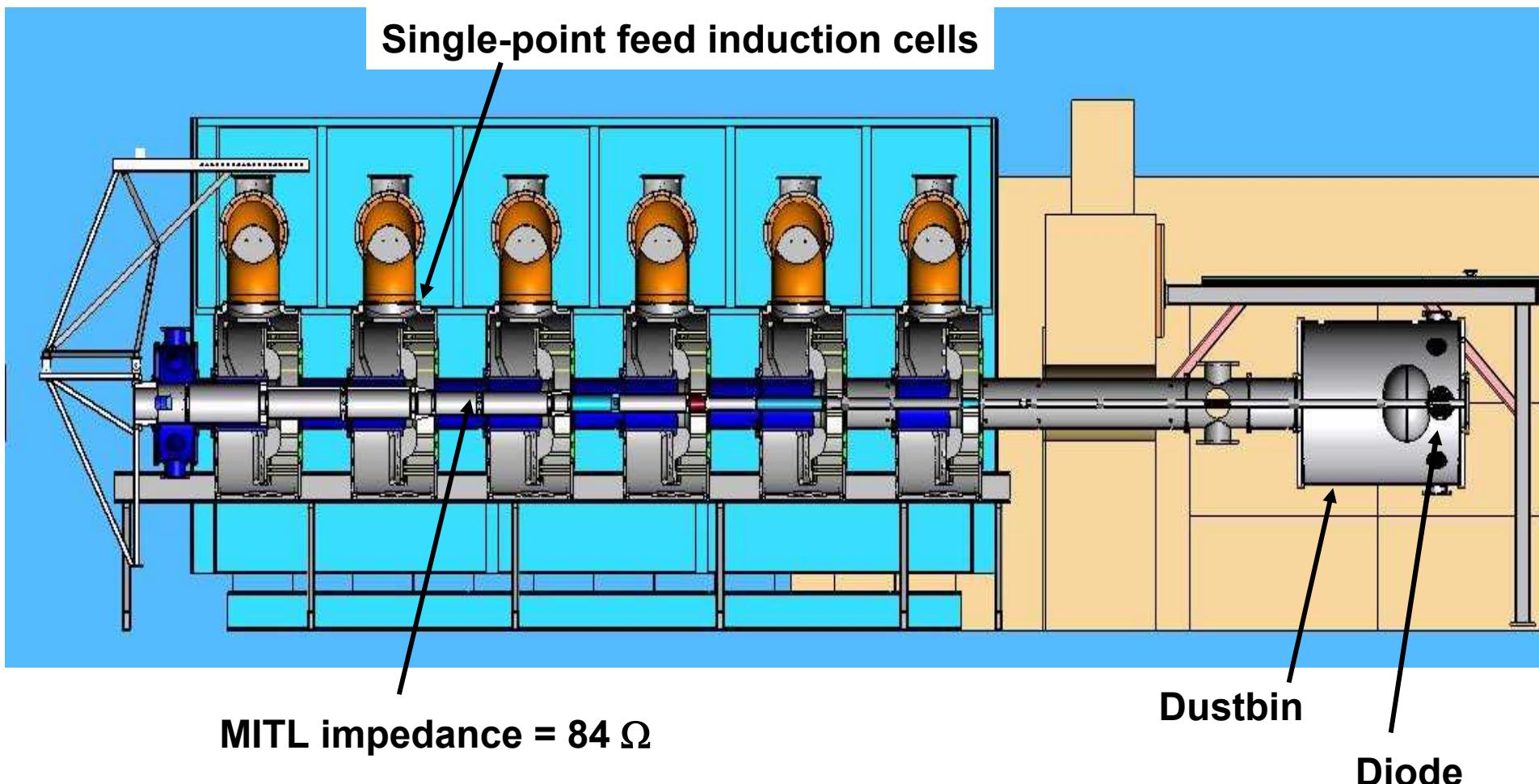
Flexible accelerator producing:  
4.5-11 MV, 125-190 kA, 70 ns pulse.





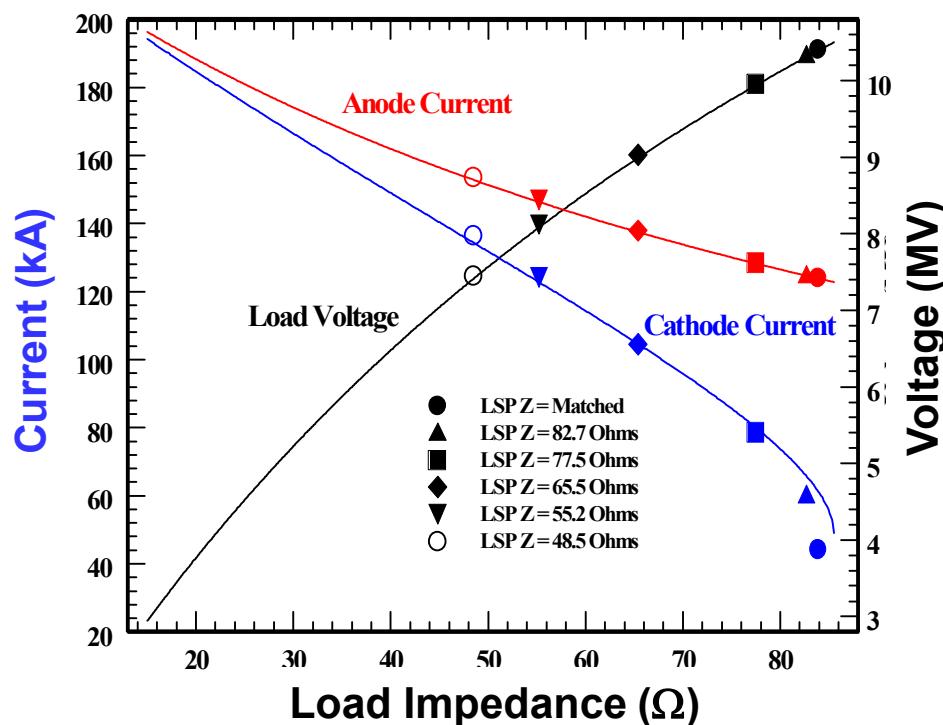
## RITS-6 Cross-section and MITL

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# RITS-6 is a flexible accelerator architecture for driving high voltage sources.

## RITS-6 MITL Operating Points



$$\text{MITL Load impedance } Z_L = V/I_A$$
$$\text{Diode impedance } Z_D = V/I_C$$

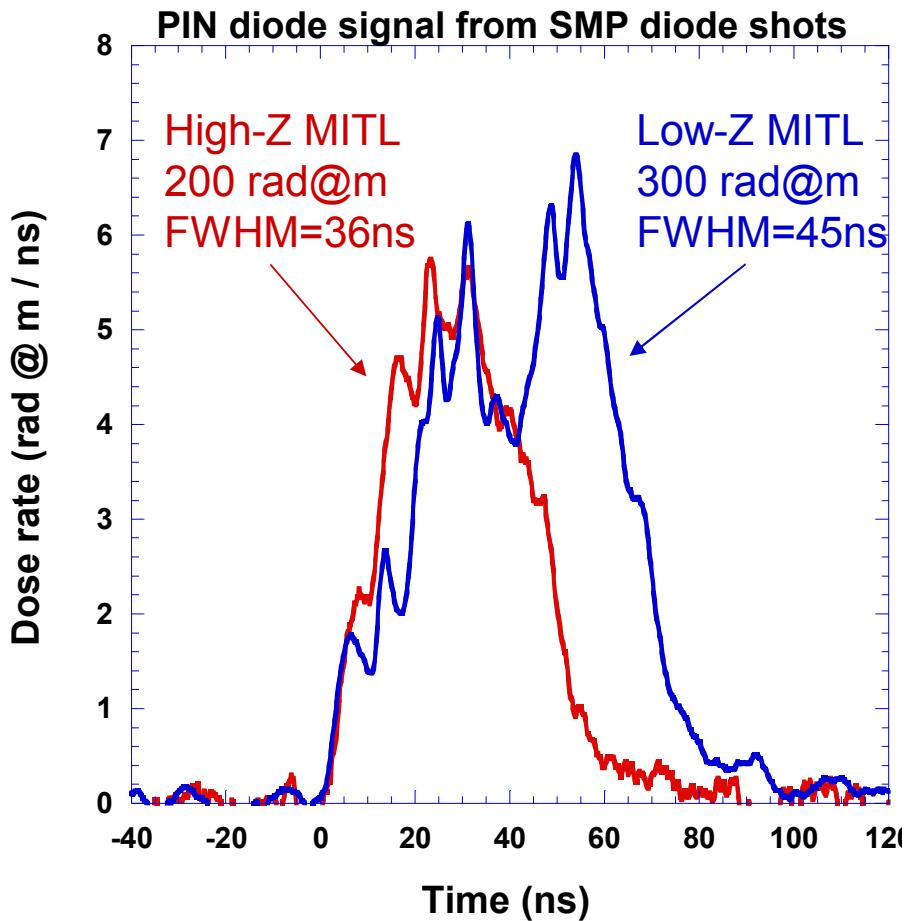
**Dose  $\sim IV^\alpha$ ,  $1 < \alpha < 3$ :** we can increase dose by either increasing current, voltage or both

Non-linear MITL impedance  $V=I(Z)$  enables efficient drive for a variety of diode impedances. Can obtain 300% increase in diode current for only 30% decrease in voltage!

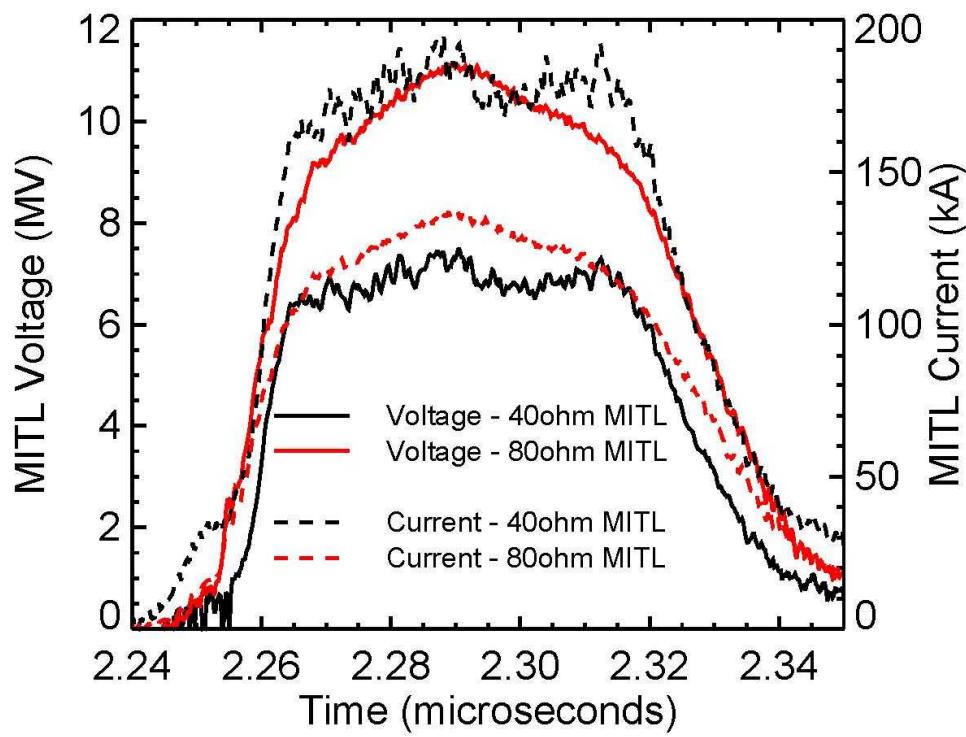
We can also use different MITL's to enhance power coupling

# Minor changes to accelerator architecture increase power coupling to source

Designed a 42 Ohm MITL (vs. 82 Ohm) to thread the center of accelerator



Low impedance MITL used to couple power to low impedance sources

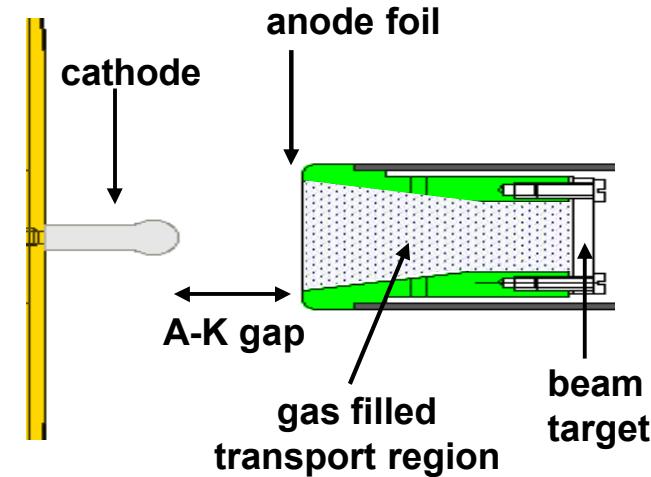


# High Impedance Diodes (~200+ Ohms)

## Dose $\propto IV^{2.65}$

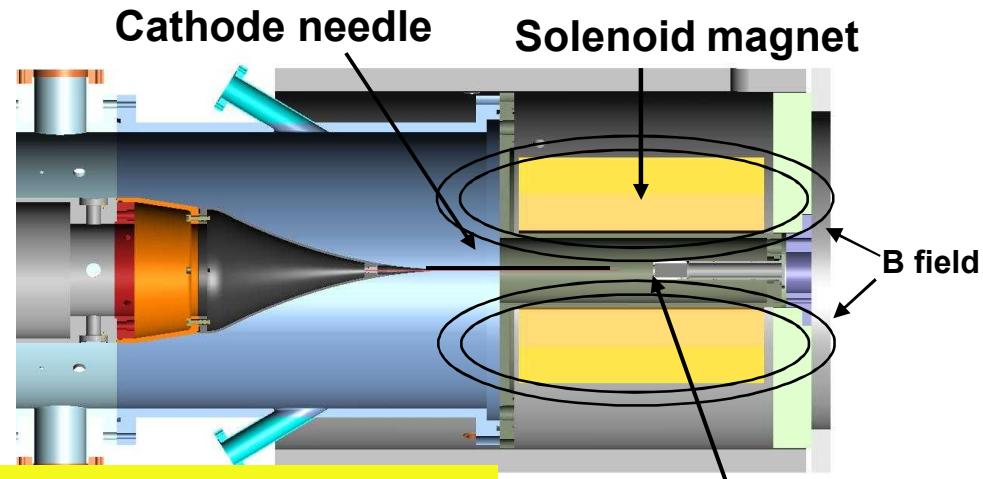
### Paraxial Diode:

e-beam accelerated in vacuum A-K gap and transported to the target in gas.



### Immersed $B_z$ :

e-beam accelerated in vacuum and transported directly to anode/target. Beam is confined by strong 40T  $B_z$  magnetic field.



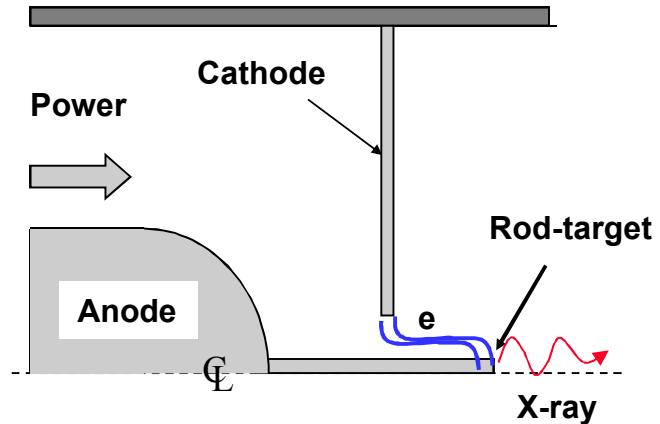
These diodes produce high radiation dose because of their high operating voltage and  $\sim$  normal incidence on target!

# Low Impedance Diodes ( $\sim 50$ Ohms)

## Dose $\propto IV^{1.2-2}$

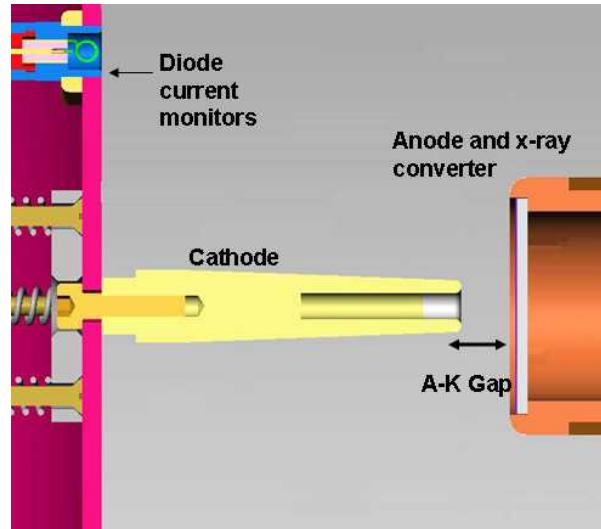
### Rod-Pinch:

Bi-polar diode (e+ions). e-beam is self-field insulated and propagates to tip of anode rod/target.



### Self-Magnetic Pinch:

Bi-polar diode (e+ions). e-beam is pinched onto anode/target by self-magnetic  $B_0$  field.



These diodes produce small spots but less radiation dose because of their high average angle of incidence on target!

# Paraxial diode: beam propagation in overdense gas $n_b/n_g \ll 1$ . Gas-cell acts as a $1/4$ betatron focusing lens<sup>1</sup>

Gas breakdown sufficient for complete charge neutralization but incomplete current neutralization.

$$\frac{d^2 r_b}{dz^2} \approx -\frac{1}{r_b} \frac{2I_{\text{net}}}{I_A} + \frac{\epsilon^2}{r_b^3}, \quad I_{\text{net}} = I_b + I_{\text{plasma}}$$

For  $\epsilon^2 \ll 2R^2 I_{\text{net}}/I_A$

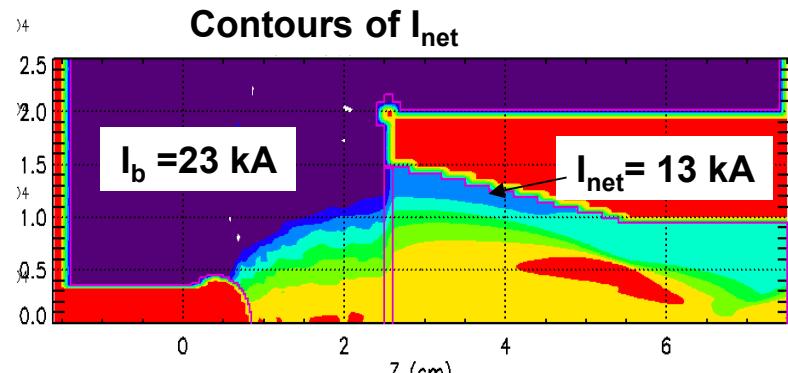
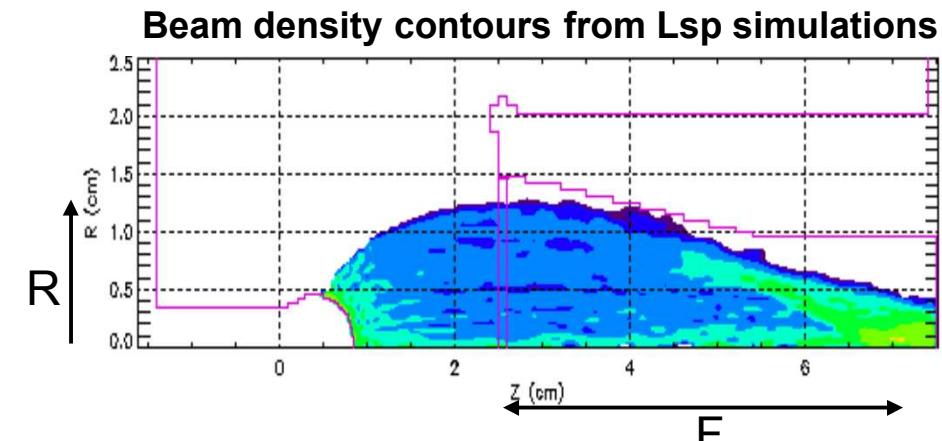
$$F \approx \frac{R}{2} \sqrt{\frac{\pi I_A}{I_{\text{net}}}}, \quad I_A = 17\gamma\beta \text{ (kA)}$$

$$\propto \sqrt{\frac{\gamma}{I_{\text{net}}}}$$

Net current (beam + plasma)  $I_{\text{net}} = crB_\theta/2$

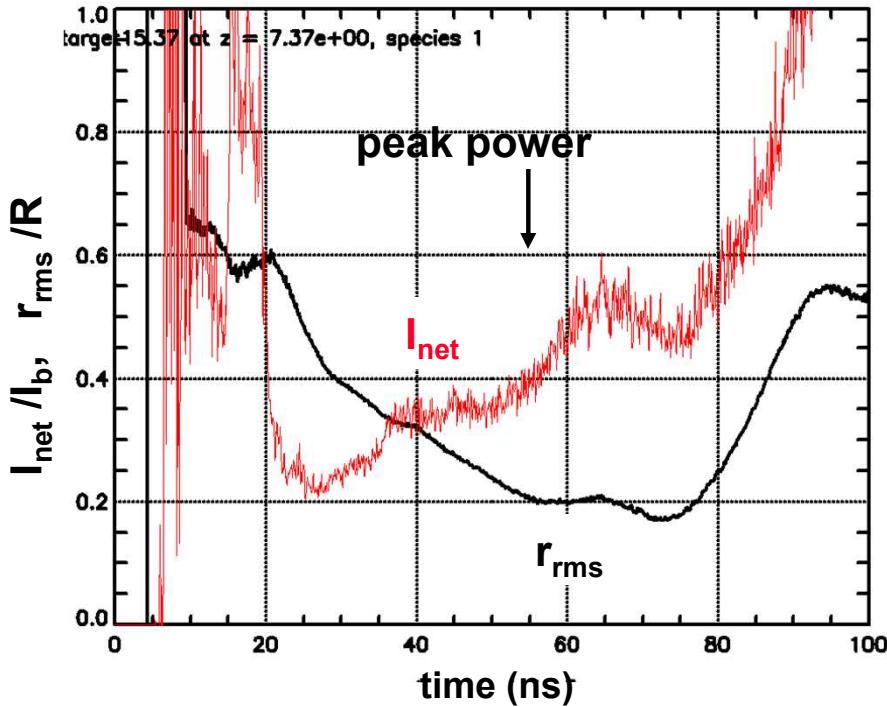
$$\frac{\partial B}{\partial t} = -\nabla \times \frac{c}{4\pi e n_e} \left( \nabla \times B - \frac{4\pi}{c} j_b \right) \times B + \nabla \times \frac{c^2}{4\pi \sigma} \left( \nabla \times B - \frac{4\pi}{c} j_b \right)$$

Hall current advection
Resistive diffusion



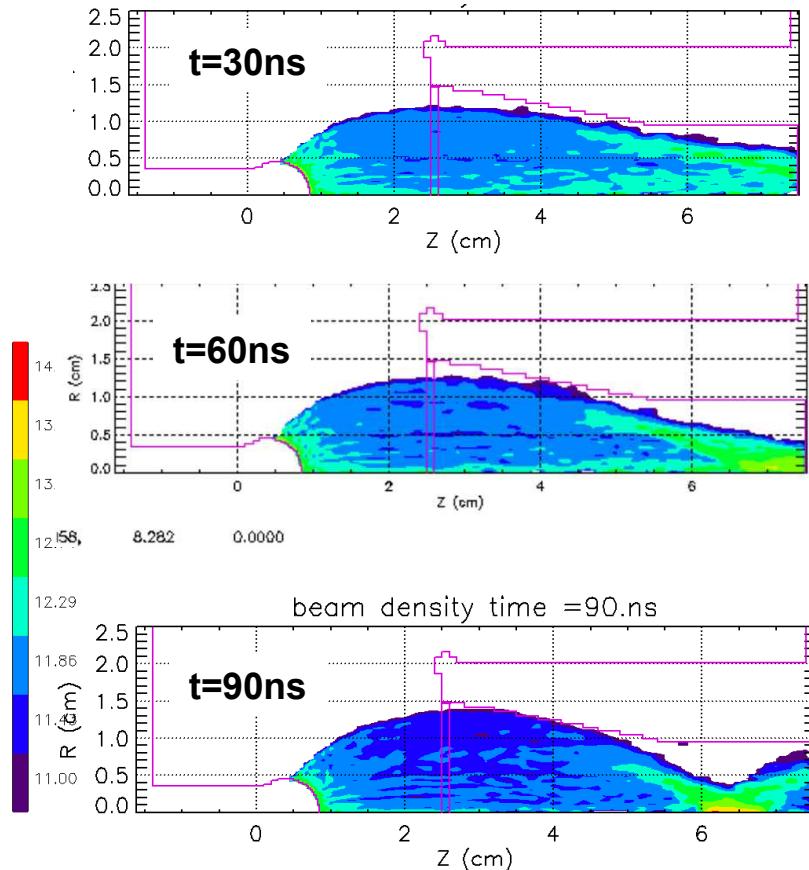
# Time dependence of $I_{\text{net}}$ causes a sweeping focus!

$$F(t) \approx \frac{R}{2} \sqrt{\frac{\pi I_A}{I_{\text{net}}(t)}}$$



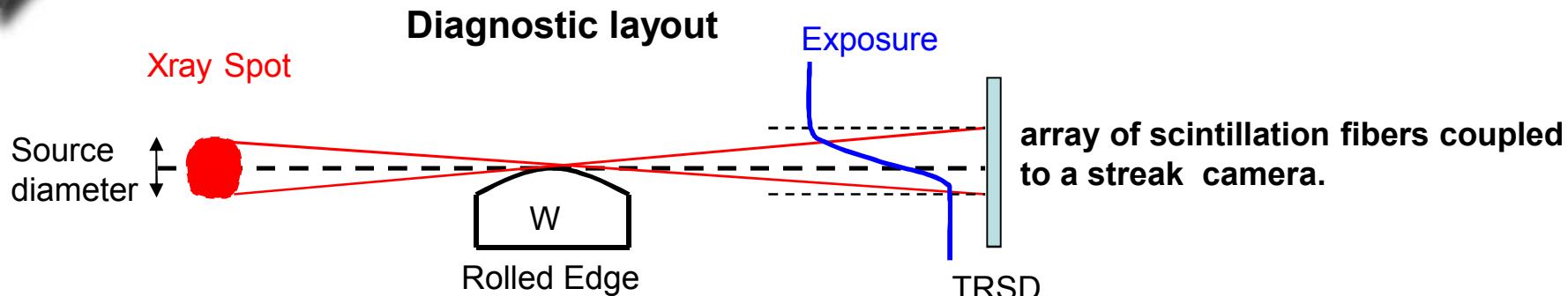
Beam rms radius and  $I_{\text{net}}$  vs time. At peak power,  $I_{\text{net}} = 9 \text{ kA}$ ,  $r_{\text{rms}} = 0.2 \text{ cm}$

Contours of beam density



Focal sweeping is a primary contributor to larger than desired time integrated spots.

# Time-resolved x-ray spot diagnostic measures beam sweep on paraxial diodes



**The baseline AWE x-ray source is being improved**

Hybrid 3D simulations

Time resolved spot diagnostic

Spectroscopy for plasma diagnostics

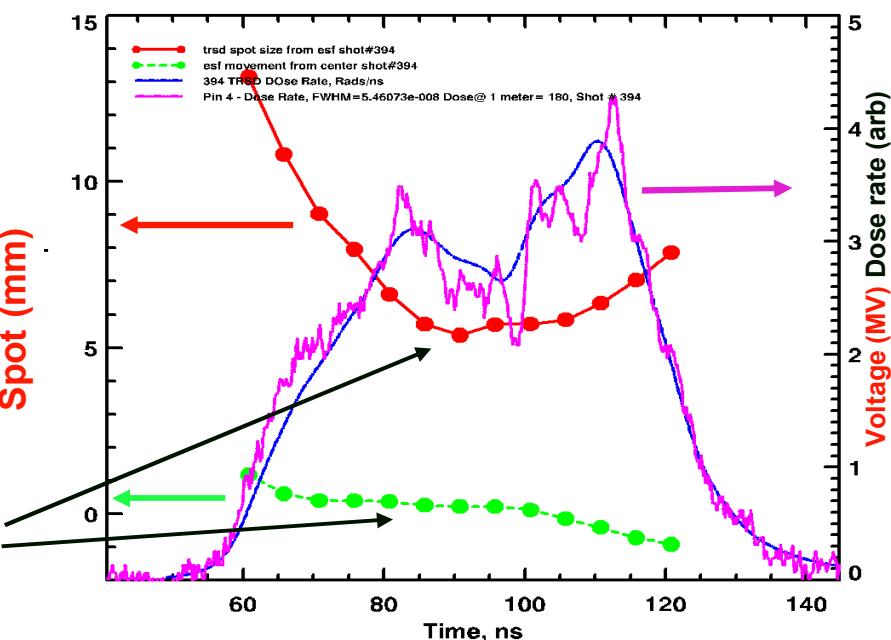
Expect to decrease the spot by a factor 2.

## 11 MeV Paraxial source on RITS

500 rads @ 1m from a

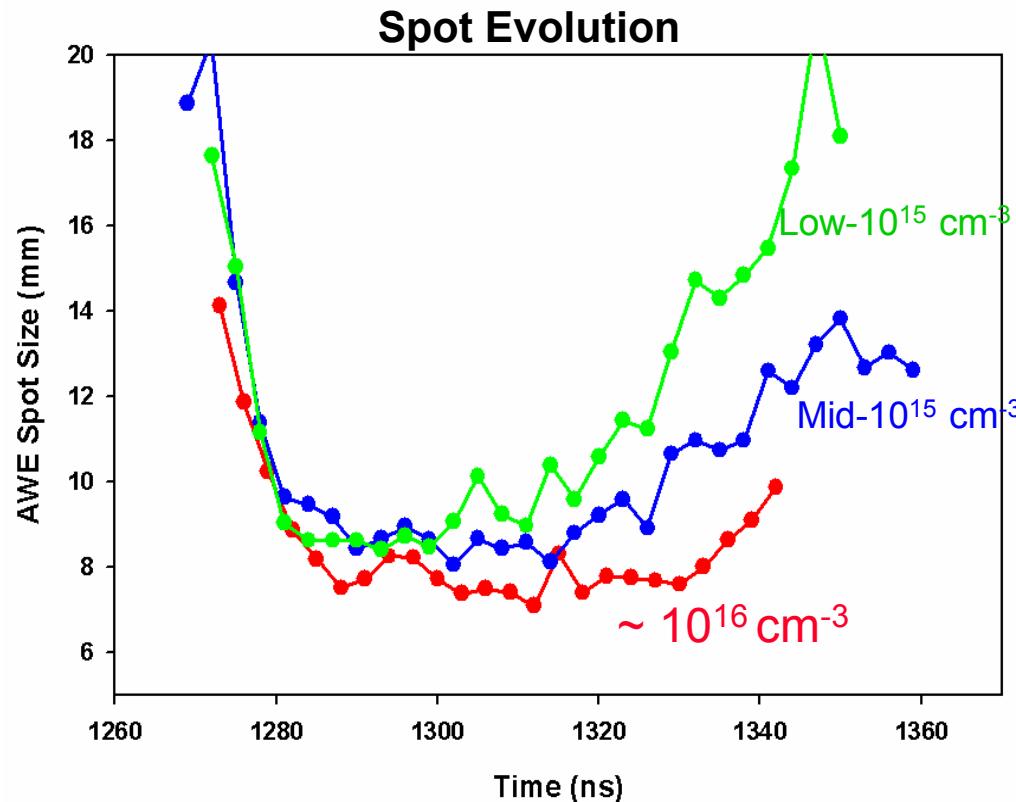
7.0 mm (0-100% AWE) spot

First measurements of  
beam sweep and spot  
wander



# Demonstrated Plasma-filled focusing cell controls time dependent spot growth

Theory and simulations<sup>1</sup> suggest replacing gas-filled transport cell with a highly pre-ionized plasma limits beam sweep. Confirmed on RITS Accelerator



see K. Hahn<sup>2</sup> et al. poster

1. D. Welch, D.V. Rose, B.V. Oliver et al, Phys. Plasmas, **11**, 2004

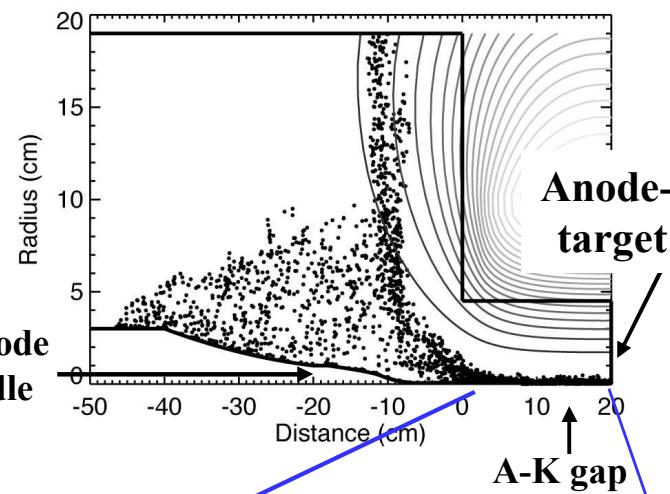
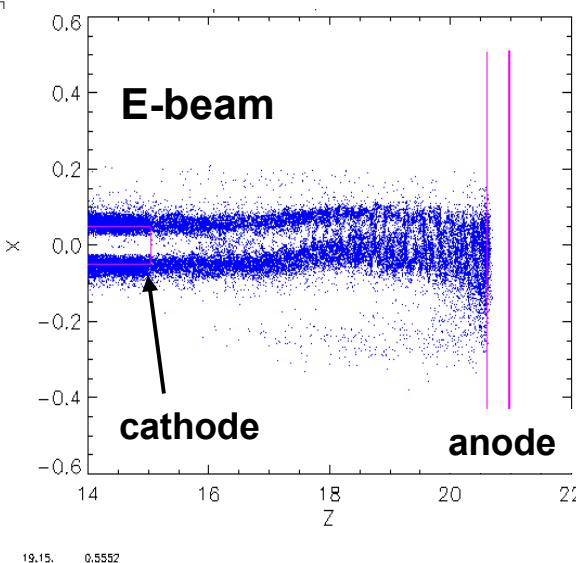
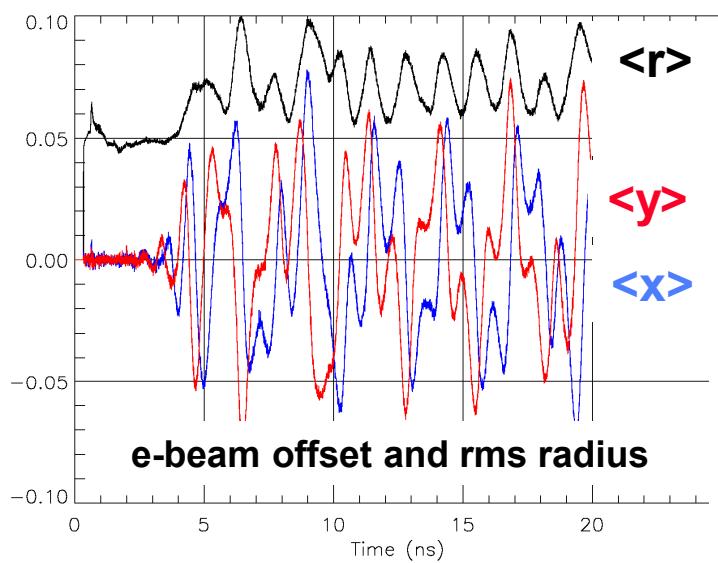
2. K. Hahn, PhD thesis, Univ. of New Mexico, 2006

# The ion-hose instability limits spot-size in immersed- $B_z$ diodes

**Immersed- $B^1$ :** High dose production because beam incidence angle  $\theta_m \sim 0$

**spot:** spot is determined by ion-hose saturation amplitude

$$\langle r_{\text{sat}} \rangle \approx \frac{c}{\Omega_e} \sqrt{2\gamma \frac{I_b}{I_A}}$$

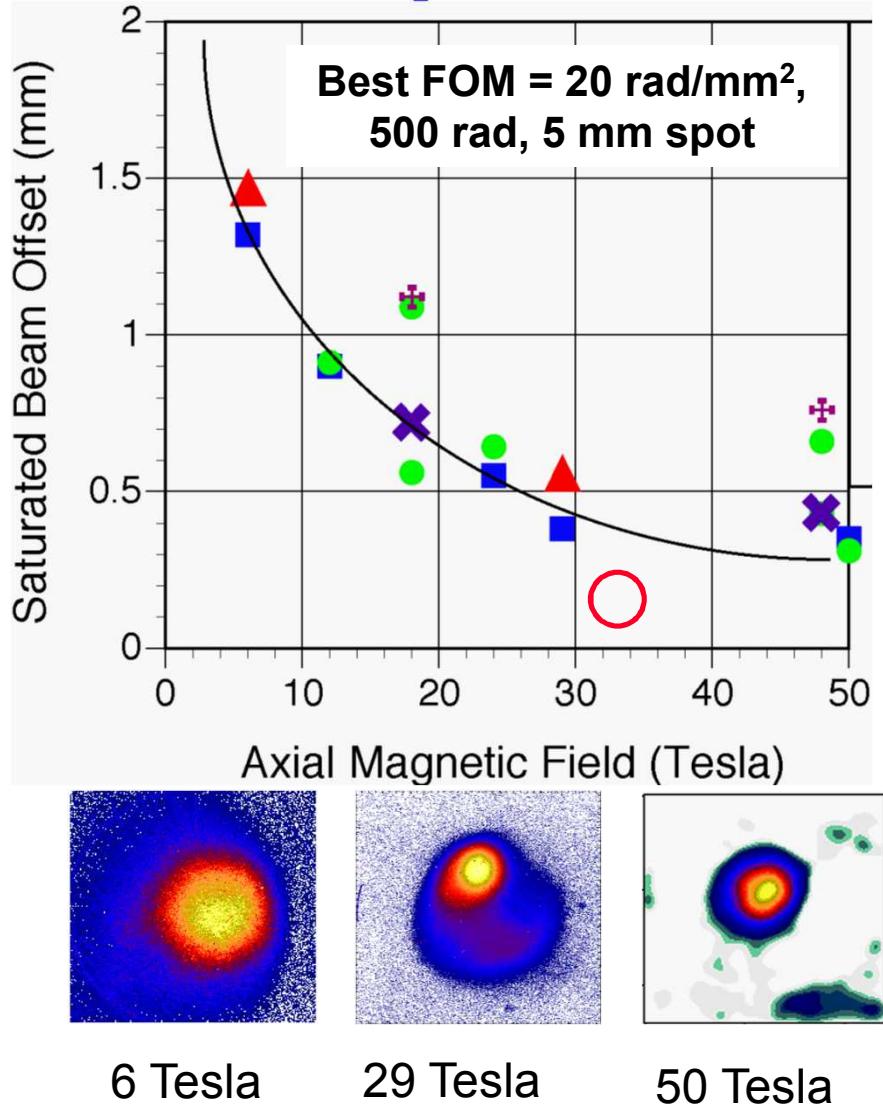
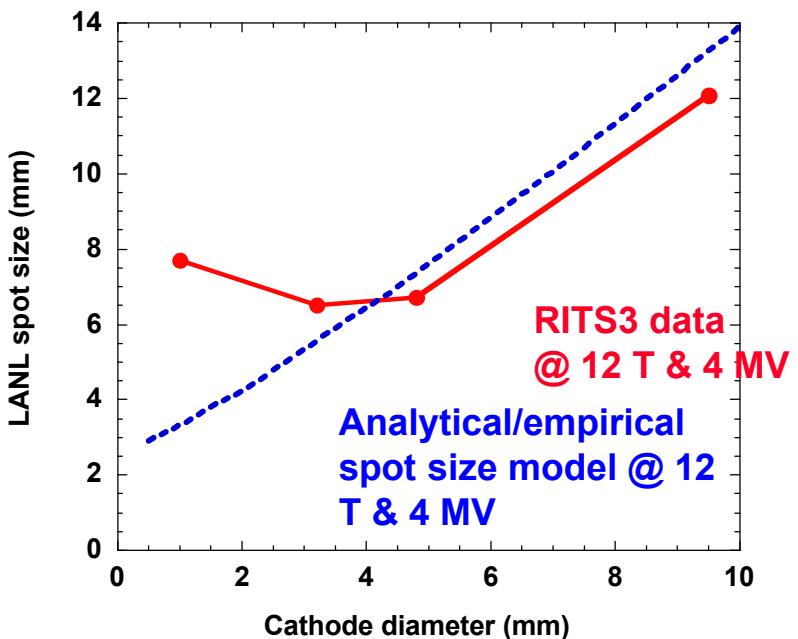


3-D PIC simulations of immersed- $B$  diode electron and ion dynamics

# Nonlinear saturation of ion-hose $\propto 1/B_z$ . But small spots influenced by ions.

Radiographic spot size decreases as  $\sim 1/B$ !.....up to some critical spot size!<sup>1</sup>. Time of flight suggests ion interactions not plasma interactions.

Scaling is not reproduced for small spots!

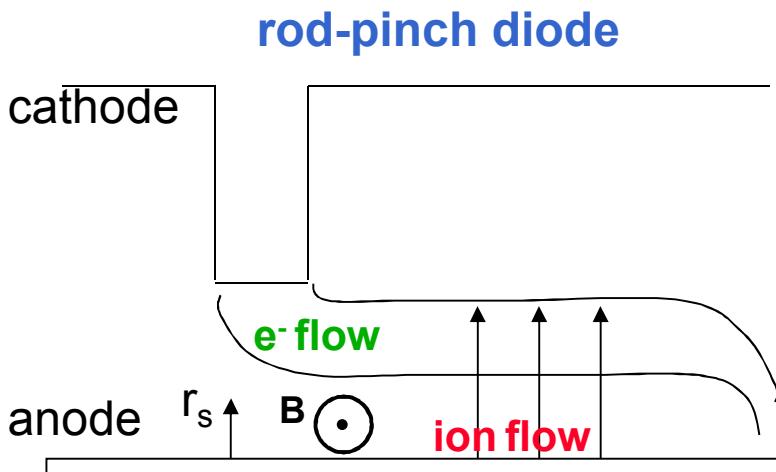


Spot data courtesy of J. Maenchen<sup>2</sup>

1. D.C. Rovang et al., Phys. Plasmas **14**, 113107 (2007)
2. J. Maenchen, et al. Proc. IEEE Trans. **92**, 1021, (2004)



# The Rod-Pinch is a self-magnetically insulated diode that provides small spots



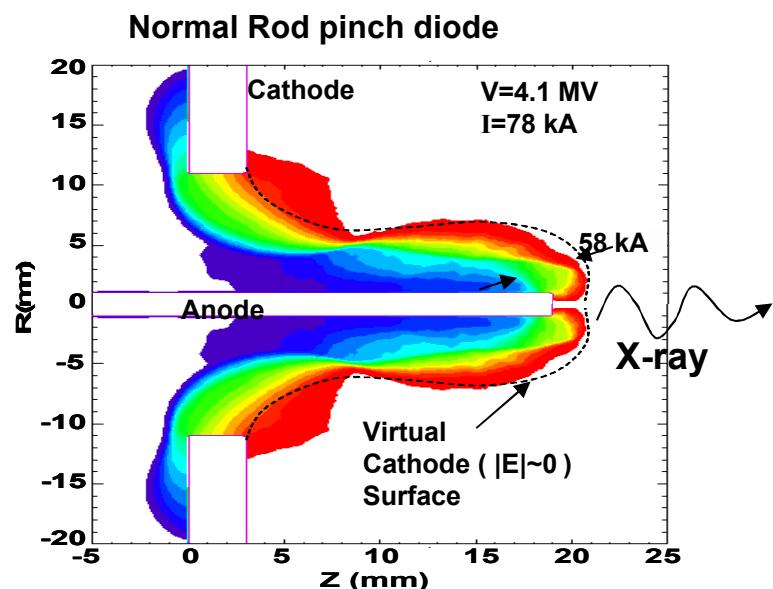
Operation is described by self-insulated flow theory with the inclusion of ions<sup>1,2</sup>.

Spot determined by rod diameter

Diode current well modeled by critical current formulation:

$$I = \alpha I_{\text{crit}}, \quad 2.0 < \alpha < 2.6$$

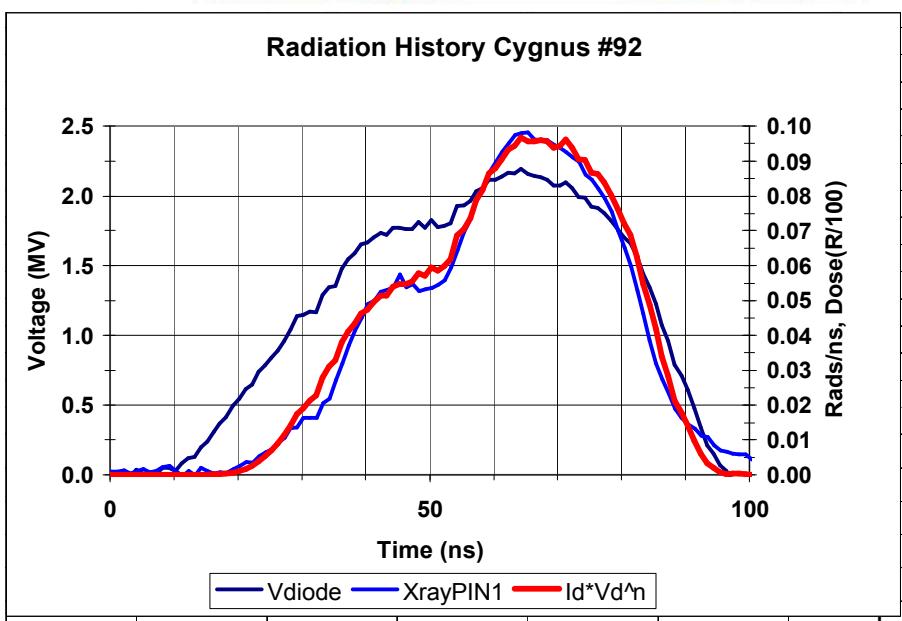
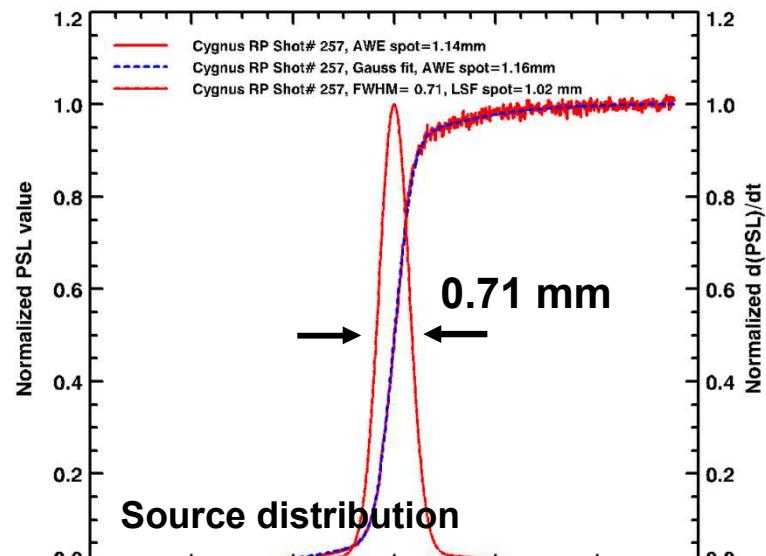
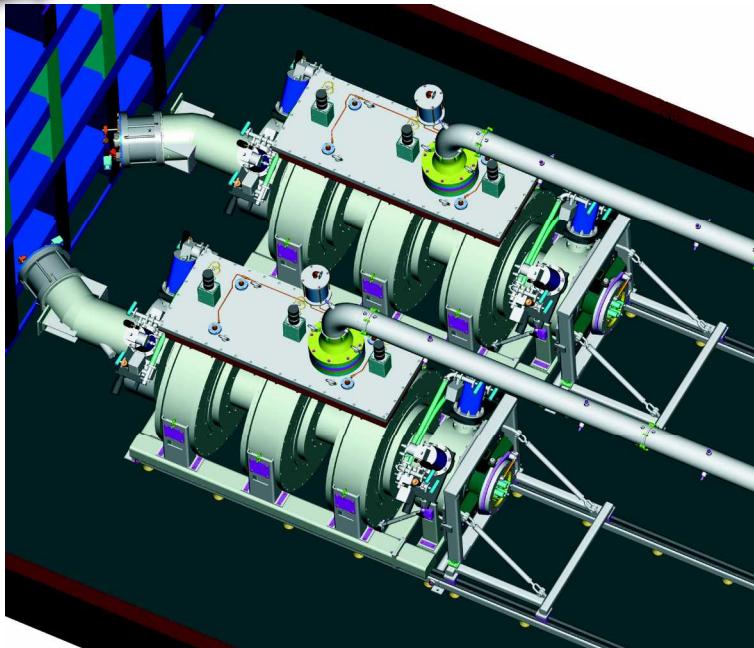
$$I_{\text{crit}} = 8.5 \frac{\sqrt{\gamma^2 - 1}}{\ln(r_c / r_a)} \text{ kA}, \quad \gamma = 1 + eV/mc^2$$



1. G. Cooperstein et al. Phys. Plasmas, **8**, 4618 (2001)
2. B.V. Oliver et al. Phys. Plasmas, **11**, (2004);

Fig. courtesy of S. Swanekamp, NRL

# Cygnus is a dual axis IVA-driven high resolution radiographic system



# Alternative source development for the future: Negative Polarity Rod-Pinch

Dose at  $0^\circ$  scales weakly with voltage<sup>1</sup>!

$$D \text{ (rad)} \propto \int I_e V^{1.25} dt$$

Dose at  $180^\circ$  in backwards direction is maximized<sup>2</sup>

$$D \text{ (rad)} \propto \int I_e V^{2.22} dt$$

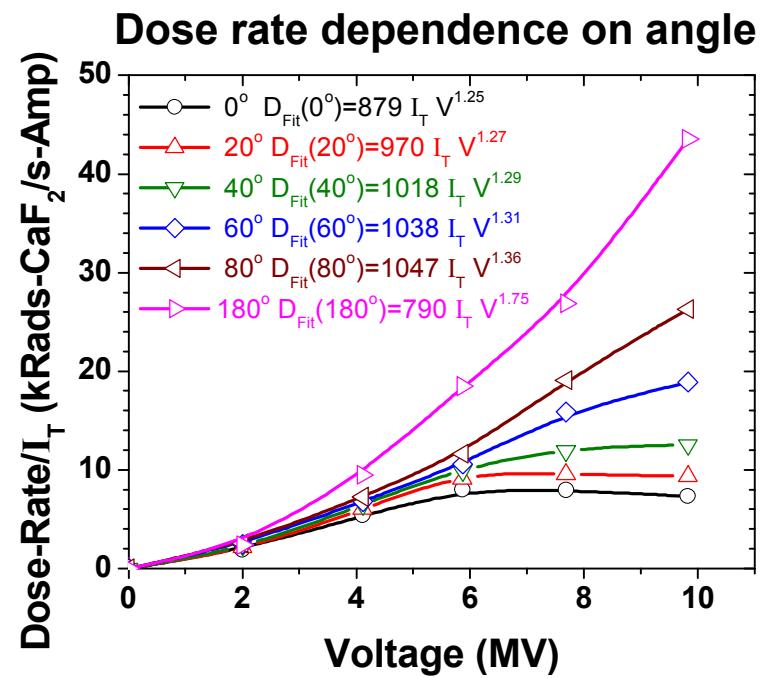
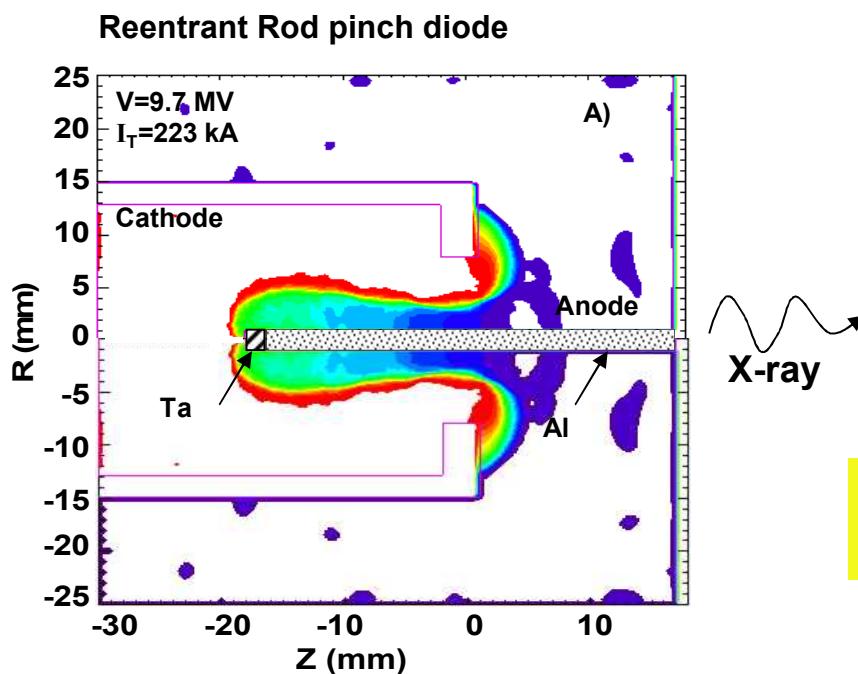


Fig. courtesy of S. Swanekamp, NRL

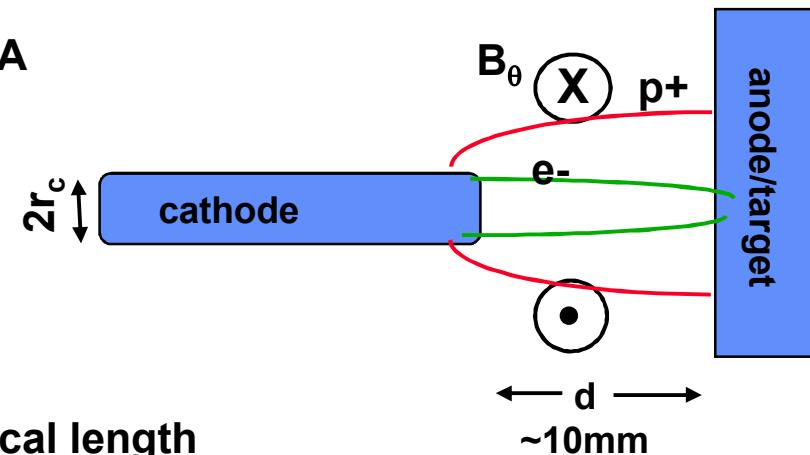
Should be capable of producing  $> 150 \text{ rad}$   
with  $< 2\text{mm}$  spots, FOM  $> 35 \text{ rad/mm}^2$

1. D.V. Rose et al. JAP **91**, 3328 (2002)

2. S.B Swanekamp, G. Cooperstein, J.W Schumer et al. IEEE Trans. Plasma Sci. **32**, 2004 (2004)

# Self-Magnetic pinch diode acts similar to a $\frac{1}{4}$ betatron focusing cell, but in vacuum!

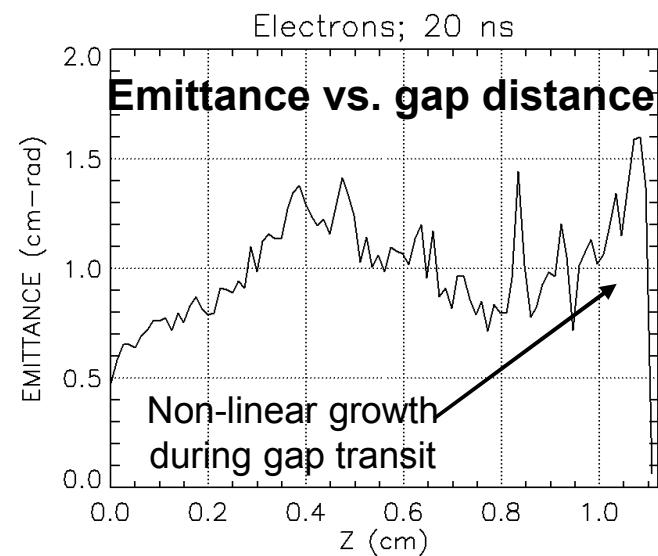
Relativistic Bi-polar diode. High current  $I_b \sim 150$  kA



Self-magnetic  $B_\theta$  pinches the beam on target. Focal length function of total current. Spot determined by emittance which is driven by non-linear field structure

$$F \cong \frac{r_c}{2} \sqrt{\frac{\pi I_A}{I_b}}, \quad \sim 14 \text{ mm}$$

$$\text{spot} \cong 2.4 \frac{1}{\sqrt{\pi}} \frac{\epsilon}{r_c} F \quad \sim 2.5 \text{ mm}$$

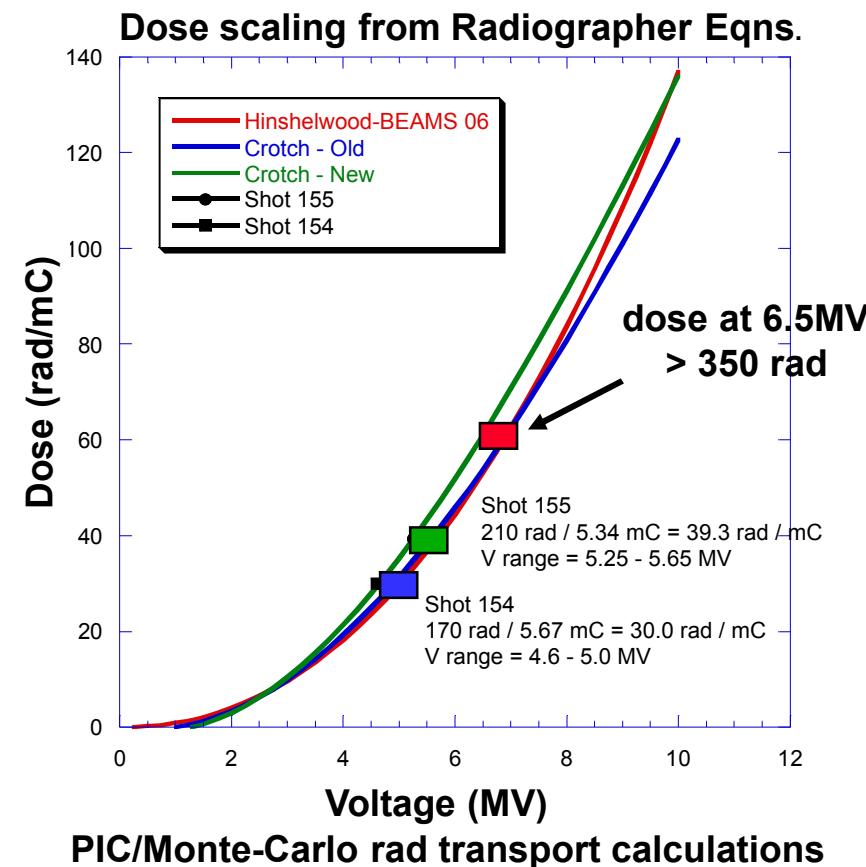
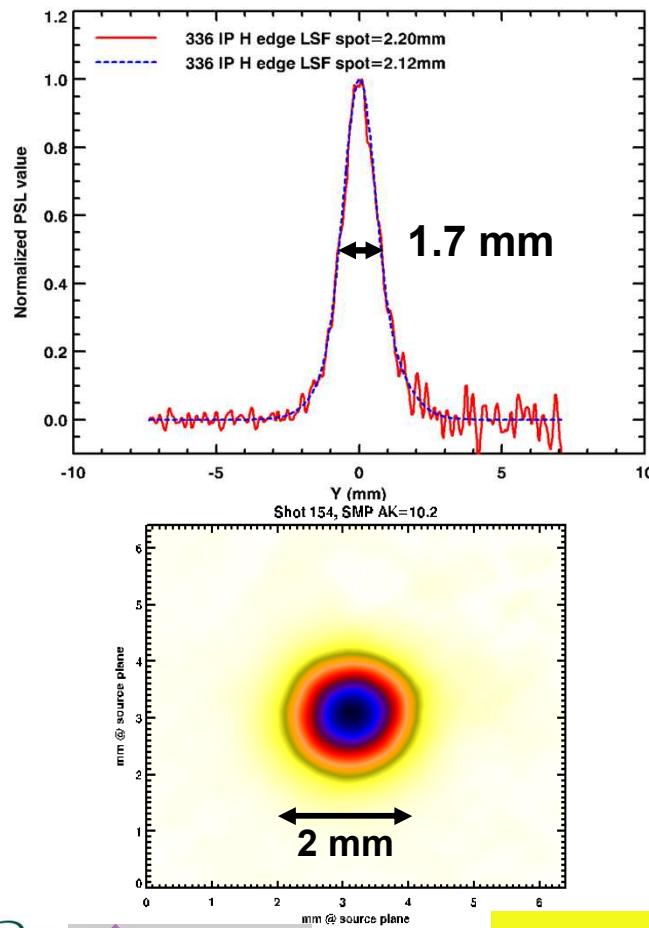


It is not influenced by ion-hose instability because the A-K gap is too small for growth.

# Self-pinch diode is one of our brightest sources!

SNL, AWE, NRL team have demonstrated 350+ rads from a 1.7-mm FWHM source distribution on RITS-6 Accelerator with 6.5 MeV endpoint energy.

## Measured x-ray source spot



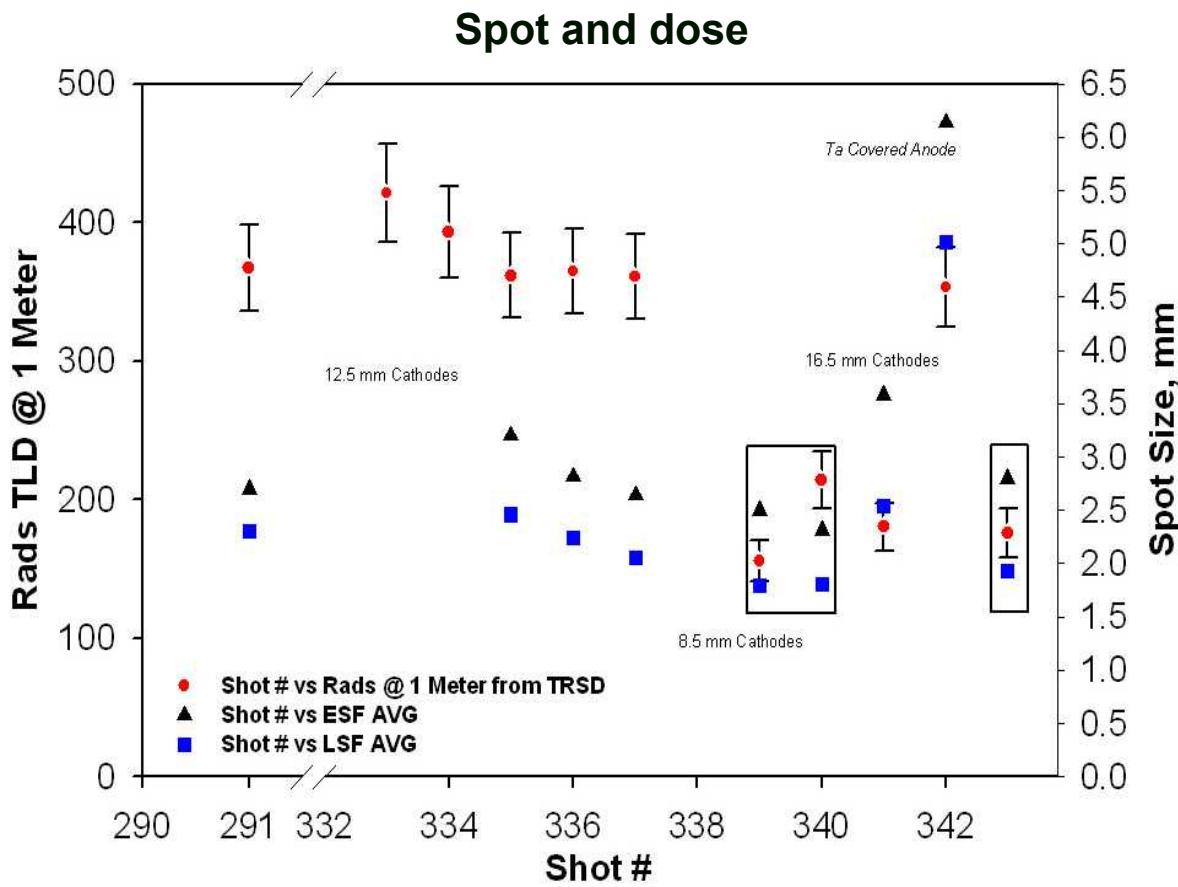
Demonstrated brightness > 50 rad/mm<sup>2</sup>

# Self-pinched diode geometric changes can produce smaller spot at reduced dose.

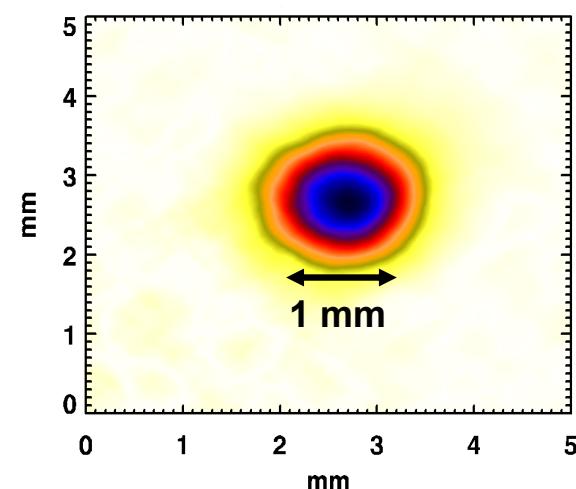
AWE definition spot =  $2.3 \text{ mm} \pm 0.2 \text{ mm}$

A LLNL definition (1.44x fwhm LSF) =  $1.75 \pm 0.1 \text{ mm}$

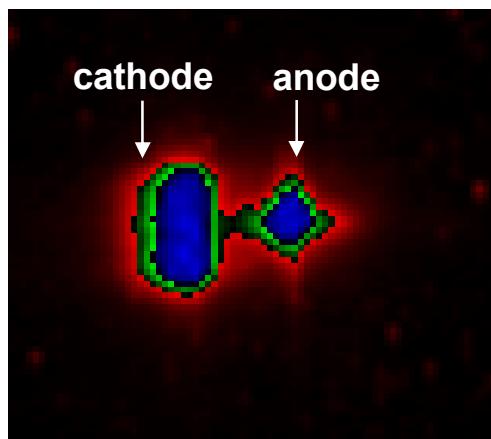
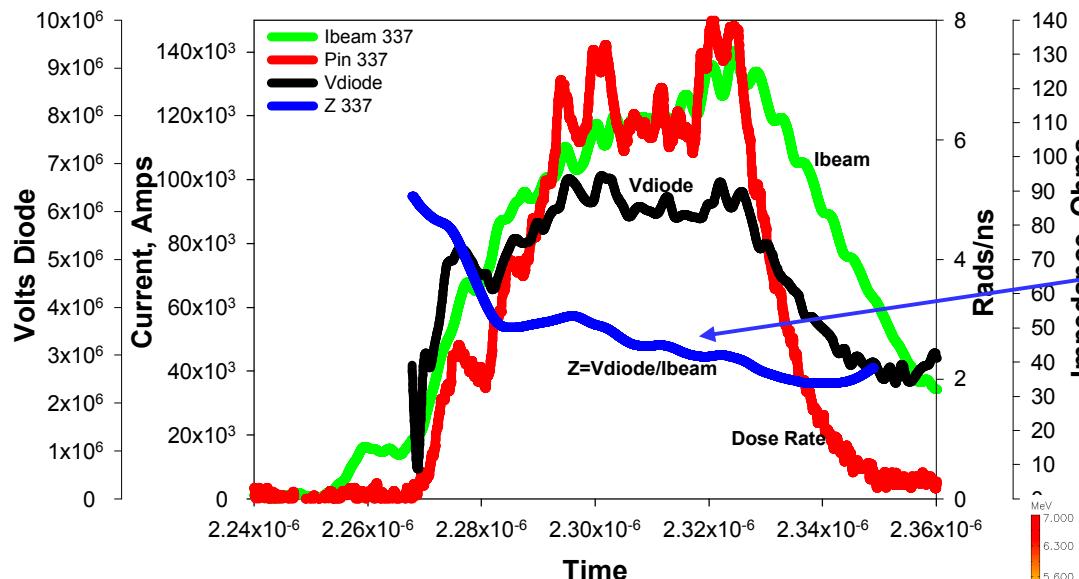
Implies a peaked core (non Gaussian) spot.



Small cathode produces 150 rad@m, 1.85mm spot



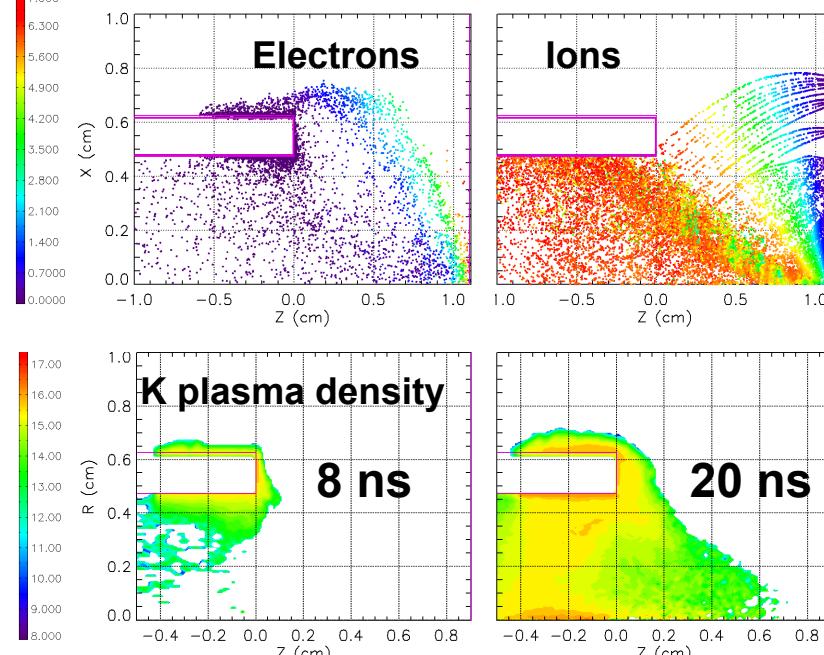
# Plasma gap closure must be controlled for brighter performance on the SMP



Light emission in A-K gap

Diode impedance decreases during pulse

Hybrid simulations of gap closure



# Future driver architectures: 1-MV Radiographic system based on LTD's

A 1-MV, 140 kA radiographic Linear Transformer Driver (LTD) has been assembled and tested in Russia and now at Sandia

Voltage adds along coaxial Magnetically insulated transmission line, like an IVA

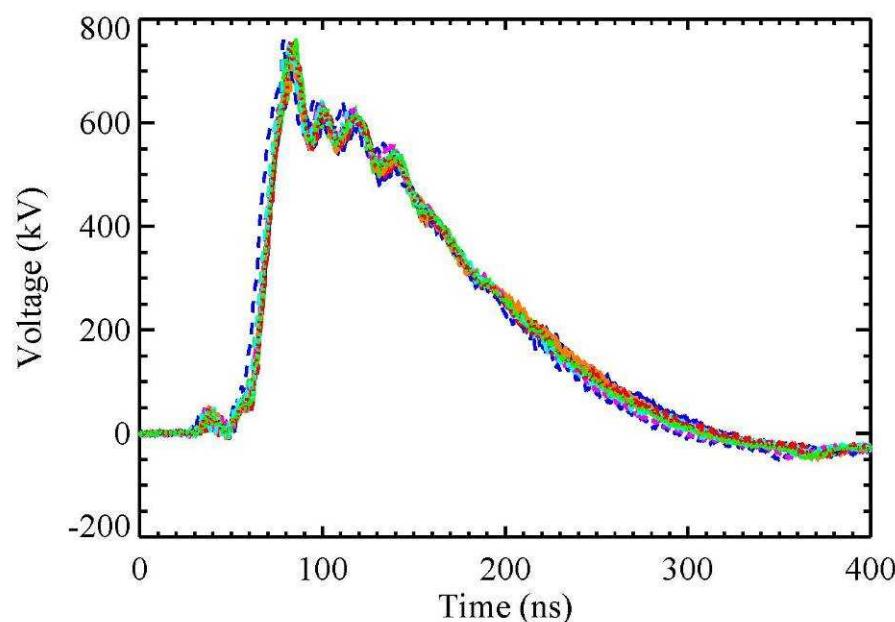
Successfully tested with electron-beam diode load for more than 300 shots



**Advantages:** lower cost and smaller foot-print:

**Status:** Demonstrated both single and stacked-cavity performance to 1 MV.

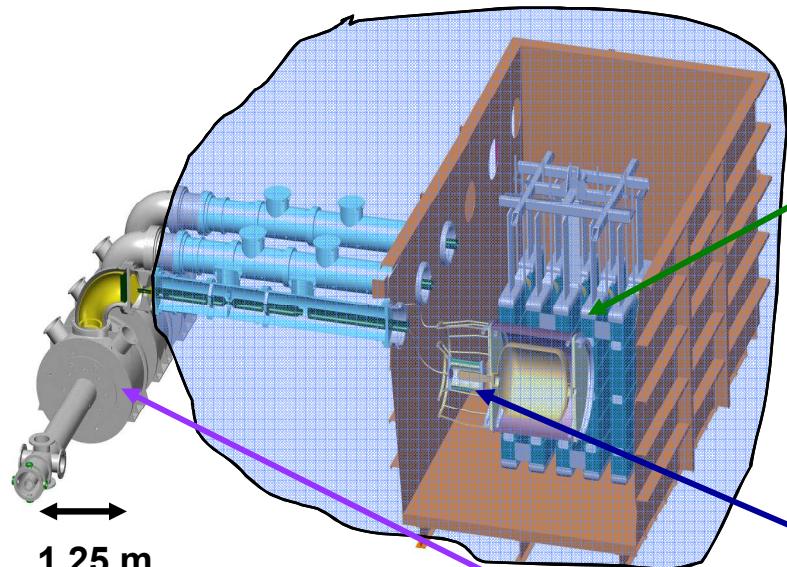
**Collaborators:** designed and built in collaboration with Institute of High Current Electronics in Tomsk, Russia and CEA and ITHPP in France.





# The LTD is much more compact than conventional IVAs

Inductive Voltage Adder (IVA)



Linear Transformer Driver (LTD)



Remove pulse formation and compression hardware

Capacitors

switches

Inductive isolation

10 m

1.25 m

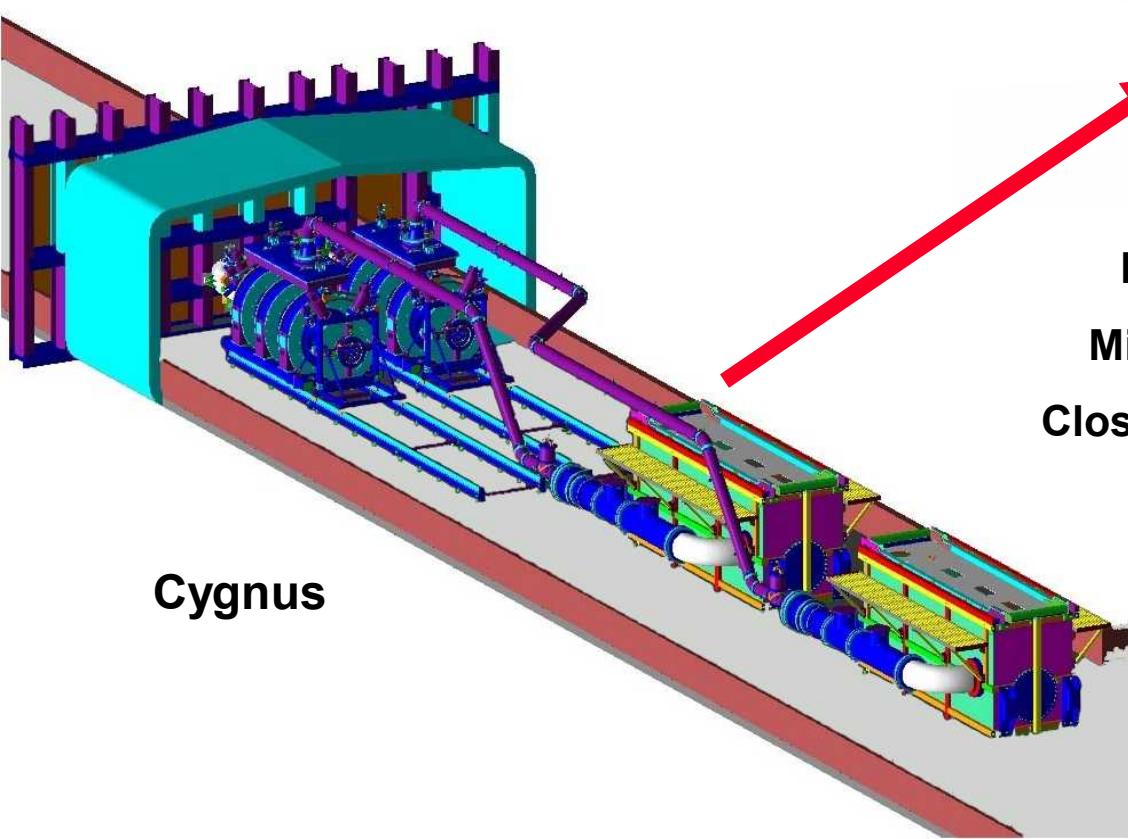
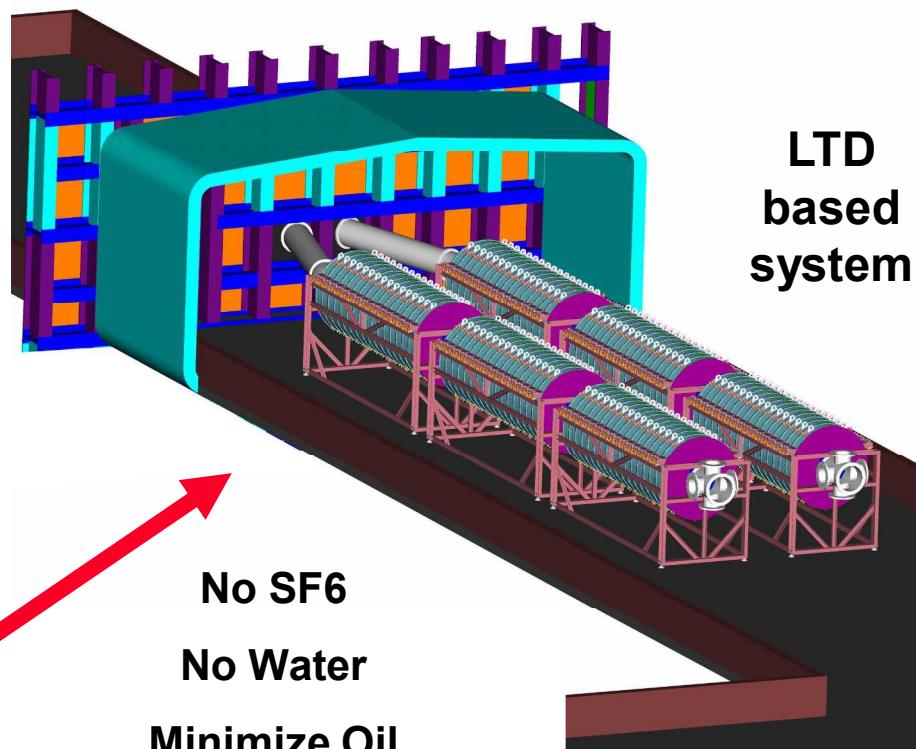
A 2-axis LTD can provide 6.5 MV, 250 rad@m,  
2.5mm spot in same foot print as Cygnus system

12' wide x 50' long x 6' high

Can replicate existing Cygnus capability

As well as provide increased capability

in steps up to 250 rad@m, 2.5-mm spot



Use either an SMP or negative polarity Rod-pinch diode at ~ 50 Ohms to drive 6.5 MeV, 130 kA diode.